The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device ~~characterized by~~ comprising:

a first film and a second film which are sequentially laminated over a substrate,

wherein the first film and the second film each has at least one layer of an insulating layer, a conductive layer, and a semiconductor layer, and

wherein a face on which the first film and the second film are in contact with each other is made of the conductive layer and at least has the same pattern.

2. (Currently Amended) A semiconductor device according to Claim 1, wherein ~~characterized in that~~ the first film and the second film have at least one of a thin film transistor, a capacitor means, a resistor means, a memory element, a thin film diode, and a photoelectric conversion element.

3. (Currently Amended) A semiconductor device according to Claim 1, wherein ~~characterized in that~~ the first film and the second film have a display portion including a plurality of pixels arranged in a matrix.

4. A(Currently Amended) A semiconductor device according to Claim 3, wherein ~~characterized in that~~ an EL element or liquid crystal is used for the display portion.

5. (Currently Amended) A semiconductor device according to Claim 1, wherein the substrate ~~may have~~ has a flat surface or a curved surface.

6. (Currently Amended) A method for manufacturing a semiconductor device

~~characterized by~~ comprising ~~the steps of~~:

forming a first film ~~in which~~ having a first insulating layer, a first conductive layer, and a first semiconductor layer ~~are formed~~ over a first substrate;

forming a second film having a second insulating layer, a second conductive layer having at least the same pattern as the first conductive layer, and a second semiconductor layer over a second substrate;

fixing the first film to a third substrate after peeling the first film off from the first substrate; and

laminating the second film over the first film fixed to the third substrate after peeling the second film off from the second substrate,

wherein the first film and the second film are connected by contact of the same patterns in the step of laminating.

7. (Currently Amended) A method for manufacturing a semiconductor device according to Claim 6, wherein ~~characterized in that~~ the first conductive layer and the second conductive layer each have at least the same pattern on a face on which the first film and the second film are in contact with each other.

8. (Currently Amended) A method for manufacturing a semiconductor device according to Claim 6, wherein ~~characterized in that~~ a peel layer is formed between the first substrate and the first film.

9. (Currently Amended) A method for manufacturing a semiconductor device according to Claim 6, wherein ~~characterized in that~~ a step of removing the peel layer is provided between the step of peeling the first film off from the first substrate and the step of fixing the first film to the third substrate.

10. (Currently Amended) A method for manufacturing a semiconductor device

according to Claim 6, wherein ~~characterized in that~~ a peel layer is formed between the second substrate and the second film.

11. (Currently Amended) A method for manufacturing a semiconductor device according to Claim 6, wherein ~~characterized in that~~ a step of removing the peel layer is provided between the step of peeling the second film off from the second substrate and the step of laminating the second film over the first film.

12. (Currently Amended) A method for manufacturing a semiconductor device according to Claim 6, wherein ~~characterized in that~~ the third substrate has a flat surface or a curved surface.

13. (Currently Amended) A method for manufacturing a semiconductor device ~~characterized by~~ comprising ~~the steps of~~:

forming a first film ~~in which~~ having a first insulating layer, a first conductive layer, and a first semiconductor layer ~~are formed~~ over a first substrate;

forming a second film having a second insulating layer, a second conductive layer having at least the same pattern as the first conductive layer, and a second semiconductor layer over a second substrate;

peeling the first film off from the first substrate by fixing a third substrate to the first film;

fixing the peeled first film to a fourth substrate;

peeling the second film off from the second substrate by fixing the second film to a fifth substrate; and

laminating the peeled second film over the first film fixed to the fourth substrate,

wherein the first film and the second film are connected by contact of the same patterns with each other in the step of laminating.

14. (Currently Amended) A method for manufacturing a semiconductor device according to Claim 13, wherein ~~characterized in that~~ each of the first conductive layer and the second conductive layer ~~may each~~ at least ~~have~~ has the same pattern on a face on which the first film and the second film are in contact with each other.

15. (Currently Amended) A method for manufacturing a semiconductor device according to Claim 13, wherein ~~characterized in that~~ a peel layer is formed between the first substrate and the first film.

16. (Currently Amended) A method for manufacturing a semiconductor device according to Claim 15, wherein ~~characterized in that~~ a step of removing the peel layer is provided between the step of peeling the first film off from the first substrate and the step of fixing the first film to the fourth substrate.

17. (Currently Amended) A method for manufacturing a semiconductor device according to Claim 13, wherein ~~characterized in that~~ a peel layer is formed between the second substrate and the second film.

18. (Currently Amended) A method for manufacturing a semiconductor device according to Claim 17, wherein ~~characterized in that~~ a step of removing the peel layer is provided between the step of peeling the second film off from the second substrate and the step of laminating the second film over the first film.

19. (Currently Amended) A method for manufacturing a semiconductor device according to Claim 13, wherein ~~characterized in that~~ the fourth substrate has a flat surface or a curved surface.